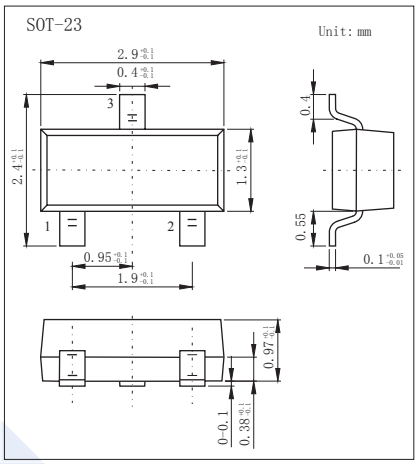
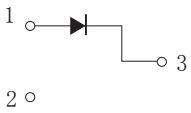
Schottky Diodes

RB400D (KB400D)



■ Features

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	V_{RM}	40	V
DC Blocking Voltage	V_R	40	
Average Rectified Output Current	Io	0.5	A
Peak Forward Surge Current	I_{FM}	3	
Power Dissipation	P_D	250	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	400	℃/W
Junction Temperature	T_J	125	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	I_R= 100 uA	40			V
Forward voltage	V_F	I_F= 500mA			0.55	
Reverse voltage leakage current	I_R	V_R=30 V			50	uA
		V_R=10 V			30	
Capacitance between terminals	C_T	V_R= 0 V, f= 1 MHz		125		pF
		V_R= 10 V, f= 1 MHz		20		

■ Marking

Marking	D3A

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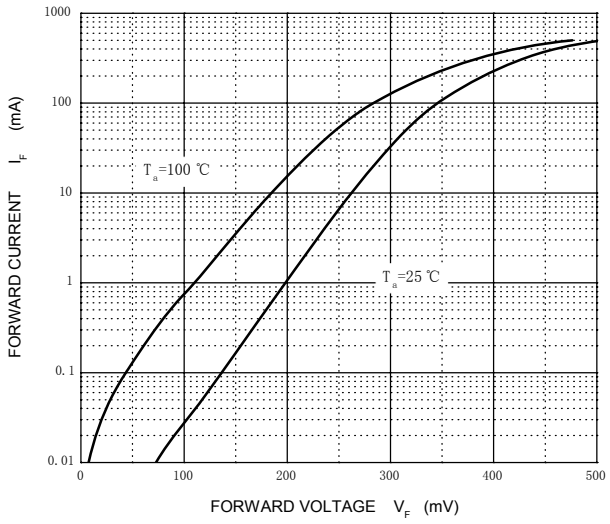
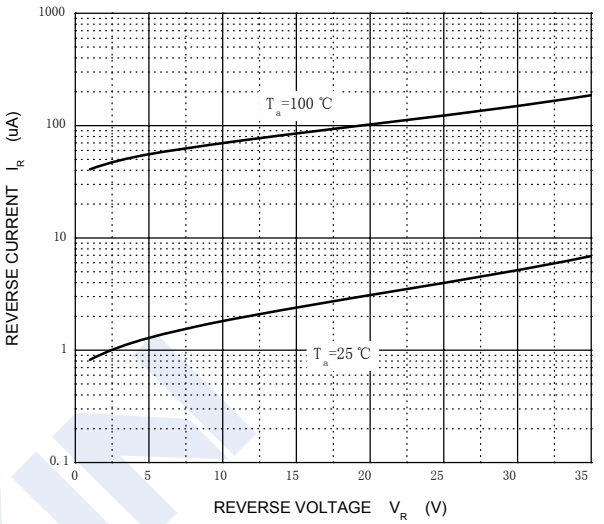
■ Typical Characterisitics

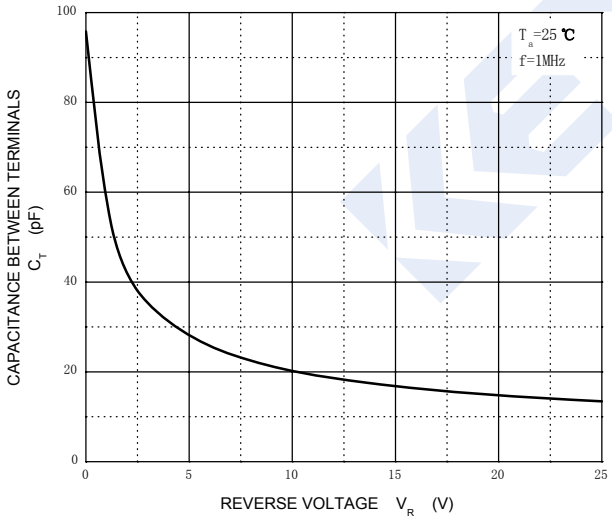
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve